On the electrostatic potential pro le in biased molecular wires

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The potential pro le across a biased molecular junction is calculated within the framework of a simple Thom as {Ferm itype screening model. In particular, the relationship between this pro le and the lateral molecular cross section is examined. We not that a transition from a linear potential pro le to a potential that drops mainly near the molecule-metal contacts occurs with increasing cross section width, in agreement with numerical quantum calculations.

I. INTRODUCTION

M olecular wires are molecules that bridge between metallic leads to form a nano-conductor whose current-voltage characteristic rejects the electronic structure of the molecule. The conductance may be controlled via its dependence on molecular properties. Equally important is the use of such molecular junctions as capacitive elements in nano-electronics.

Understanding the behavior of such junctions under potential bias is a prerequisite for elucidating their transport properties. The importance of this issue for the conductance of molecular junctions was recently emphasized by Datta and coworkers [1, 2], who have shown, within a simple Extended-Huckel (EH) model for $, ^{0}$ xylyl dithiol bridging between two gold leads, that the potential pro le (im posed on the molecule as input to the EH calculation) had a profound e ect on quantitative as well as qualitative aspects of the calculated currentvoltage characteristic. The best to experim ental results was obtained from a model that assumed (a) a at potential pro le in the interior of the molecular bridge, i.e. the potential drop occurs only at the molecule-lead contacts and (b) a symmetric distribution of the potential drop at the two contacts, i.e. for a total voltage the potential drops at each m olecular edge by =2.

This picture is supported by a recent model calculation by Mujica et al. β], where the Schrodinger equation (on the Hartree level) was solved in conjunction with the Poisson equation to yield both the electronic structure and the spatial distribution of the electrostatic potential [4]. It was found that beyond a screening distance of the order of 1 {3 atom ic lengths the potential is at along the model molecular chain.

Ab initio calculations with open system boundary conditions reveal a di erent picture: Lang and Avouris [5] have found for a chain of seven carbon atoms connecting between jellium leads that a substantial part of the voltage drop occurs along the carbon chain itself. Dam le et al. [6] have obtained similar results for a chain of gold atoms as well as for a molecular wire | phenyl-dithiol bridging between two gold electrodes [7]. In an earlier work, Pemas et al. [8] have determined that the potential along a model molecular wire is at in the absence of scattering centers, how ever these authors have derived

the local potential from a questionable local charge neutrality condition.

Recently, Weber et al. [9] have considered the voltage prole across 9,10-B is((2'-para-mercaptophenyl)-ethinyl)-anthracene coupled to two Au₂₉ clusters. Their density functional theory calculations thus go beyond the assumption of a structureless metallic electrode and take into account the species properties of the bond between the molecule and the gold atom in its local environment.

On the experimental side, Bachtold et al. [10] have used scanned probem icroscopy of both single-walled and multi-walled carbon nanotubes (SW NT and MW NT, respectively) to measure the potential drop along such nanotubes connecting between two gold electrodes. They nd an approximately linear drop of the potential in a MWNT ofdiam eter 9nm while for a metallic SWNT bundle of diam eter 2.5nm the potential is at beyond the screening regions at the tube edges. It should be emphasized that these experim ents cannot be related directly to the calculations discussed above. The nanotube length is a few m icrons and impurity and defect scattering may be e ective as is most certainly the case in the MWNT measurement. The at potential seen in the metallic SW NT m easurem ent is in fact a remarkable observation implying a very long mean free path (> 1 m) for electrons in these room temperature structures.

It is clear from the studies described above that while the computational methodology for evaluating the potential distribution on a biased molecular wire is available, a complete understanding of the way this distribution behaves in di erent wires is lacking. In this respect simple models that focus on generic properties of conducting constrictions including molecular wires are useful. The calculations of Pemas et al. [8] provide such a model that is how ever ham pered, as already stated by the restriction of local charge neutrality. The calculation of Mujica et al. [3] is also based on a generic molecular model, however, by using a 1-dim ensional Poisson equation for the electrostatic potential these authors tacitly assum e a molecular bridge whose lateral dimension is much larger than the screening length. In view of the fact that the width of molecular wires is often just a few angstroms, such an assum ption is overly restrictive. C learly, the magnitudes of the lateral width of the wire and the screening length should be important generic quantities for this issue. In

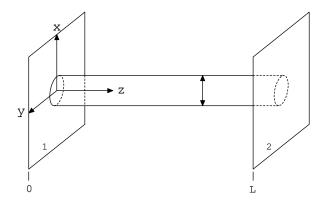


FIG. 1: The general setup contains a molecular wire modeled as a cylinder of length L and diameter between two perfect conductors with potentials $_1$ and $_2$.

this paper we present a simple model calculation that takes the relative magnitudes of these variables explicitly into account. We describe the model in Section II, present the calculation in Section III and some results and discussion in Section IV .

II. THE MODEL

The molecular wire is modeled as a cylinder of length L and diam eter of order (the exact way in which enters into the model calculation is explained below), perpendicular to and connecting between two planar metal electrode surfaces. As depicted in Fig. 1, the cylinder is oriented parallel to the z axis, with its axis going through the origin in the xy plane. The two electrodes are assum ed to be ideal conductors im plying a constant potential on the entire surface of each electrode. We set the potentials at the left and right wire-electrode interface to be $_1 = = 2$ and $_2 =$ =2, respectively. In view of (2) below, this quarantees a vanishing mean potential in z-direction and thus a neutral molecule. Finally, we restrict the discussion of the potential pro le to blocking junctions between electrodes and molecule so that no current is owing.

As in Ref. [3] we assume that the wire material does have screening capacity, and is characterized by a screening length. It should be noted that the existence, nature and size of such screening length in molecular systems is an open question with probably non-unique answer. Molecules with large gaps between their highest occupied and lowest unoccupied molecular orbitals (HOMO and LUMO) will obviously screen poorly, while highly conjugated molecules with low HOMO-LUMO gap will screen relatively well.

In the present discussion we assume that over the relevant length scales (of order ${\tt L}$) screening is described by a Poisson equation

$$r^2 = 4$$
 : (1)

A coording to the cylinder sym m etry of the molecule, the charge density $(r_k;z)$ depends on the radial distance r_k from the wire axis and the position z along the wire. In transversal direction, the charge density is assumed to be determined by a given molecular electron distribution represented by a factor $F(r_k)$. The longitudinal part depends on the potential along the molecular axis. The screening is then described by

4
$$(r_k;z) = \frac{1}{2}F(r_k)$$
 (0;z) (2)

which together with (1) will allow us to determ ine the potential pro le.

Any assumption about the functional form of F (r_k) is in fact an assumption about the connement of the molecular charge distribution in the molecular cylinder and in our generic model it is su cient to take a form that rejects the molecular thickness . O ther details of F (r_k) are expected to be of secondary in portance.

In the three-dimensional Thomas Fermi model for screening in a gas of electrons with charge e and mass me, the screening length of (2) is related to the electron density n by

$$= \frac{E_F}{6 \text{ ne}^2}^{1=2}$$
 (3)

with the Ferm ienergy

$$E_{F} = \frac{(3^{2}n)^{2=3}h^{2}}{2m_{e}}:$$
 (4)

At metallic electron densities is typically of the order of 1A. To have e cient screening in a molecular system electrons (or holes) must occupy molecular states that are e ectively delocalized over the length of the bridge. Charge doping by transfer from the metal electrode to the molecular bridge may be one source of such electrons. Their density is expected to be considerably lower than metallic, implying a larger characteristic screening length. We expect that a calculation based on (1) and (2) that uses metallic electron density to estimate will provide an upper bound on the elective screening in a molecular wire.

III. THE POTENTIAL DISTRIBUTION

U sing the m odel described in the previous section, our problem $\,$ is to solve the equation

$$r^{2} (r_{k};z) = \frac{1}{2}F(r_{k}) (0;z)$$
 (5)

in the range 0 $\,$ z $\,$ L subject to the boundary conditions

$$(r_k;0) = -2$$
 and $(r_k;L) = -2$: (6)

It is convenient to decompose the full potential

$$(\mathbf{r}_{k};\mathbf{z}) = \mathbf{0}(\mathbf{z}) + (\mathbf{r}_{k};\mathbf{z}) \tag{7}$$

into a rst term describing the bare potential

$$_{0}(z) = \frac{1}{2} \frac{z}{L}$$
 (8)

in the absence of a molecule and a second term which re ects the additional potential $(r_k;z)$ satisfying the boundary conditions $(r_k;0) = (r_k;L) = 0$.

The resulting di erential equation

$$r^{2} (r_{k};z) = \frac{1}{2}F(r_{k})[0(z) + (0;z)]$$
 (9)

m ay be solved by the Fourier ansatz

$$(r_k;z) = \frac{d^2k_k}{(2)^2} e^{ik_k r_k} \int_{n=1}^{x_k} (k_k) \sin \frac{n}{L} z$$
: (10)

A firer expressing the bare potential prole in terms of a Fourier series one arrives at

w here

$$\hat{F}(k_k) = d^2 r_k e^{ik_k r_k} F(r_k) :$$
(12)

For the potential pro le along the molecular axis, only the transversal integral over the Fourier coe cients $\hat{\ \ }_n$ (k_k) is needed which may easily be obtained from (11). Due to the symmetry of the bare potential only even Fourier coe cients are found to contribute. We thus arrive at our main result describing the potential pro le along the molecule

$$(0;z) = {}_{0}(z) - \frac{x^{i}}{n} \frac{F_{n}}{n(1+F_{n})} \sin \frac{2n}{L} z$$
: (13)

The coe cients F $_{\rm n}$ accounting for the in uence of screening are given by

$$F_{n} = \frac{1}{2} \sum_{k=0}^{Z} \frac{d^{2}k_{k}}{(2)^{2}} \frac{\hat{F}(k_{k})}{k_{k}^{2} + (2 \text{ n=L})^{2}}$$

$$= \frac{1}{2} \sum_{k=0}^{Z} dr_{k} r_{k} F(r_{k}) K_{0} \frac{2 \text{ n}}{L} r_{k}$$
(14)

where K_0 denotes a modi ed Bessel function. In the lim it of very small screening length, ! 0, it is possible to show by evaluating the sum in (13) that the potential along the wire vanishes and the entire voltage drop occurs at the interface with the electrodes.

For the following discussion, it is convenient to introduce a measure of the deviation of the voltage prole (0;z) from the linear behavior (8). Since the integral over (0;z) $_0$ (z) vanishes for a neutral molecule, we use instead

$$= \frac{12}{2L} \int_{0}^{Z} dz \quad (0;z) \quad (0;z) \quad (0;z) \quad (0;z) \quad (0;z) \quad (15)$$

This quantity is normalized such that it equals 1 if the voltage drop occurs entirely at the ends of the molecule while it vanishes for a linear potential prole. Employing (13), one may express in terms of the coecients dened by (14) as

$$= \frac{6^{1-2}}{n} \sum_{n=1}^{N} \frac{x^{n}}{n^{2} (1 + F_{n})^{2}} = \frac{f_{n}^{2}}{1 + f_{n}^{2}}$$
(16)

IV. RESULTS AND DISCUSSION

We now address the dependence of the potential prole on the width of the molecular wire and start with the limiting case of an in nitely thick molecule or, equivalently, a large number of molecules in parallel present between the two electrodes. Then, $F(r_k) = 1$ and one nds from (14)

$$F_n = \frac{L}{2 n}^2 : \qquad (17)$$

U sing

$$\frac{X^{\frac{1}{2}}}{n(n^{2} + a^{2})} = \frac{\sinh (a(x))}{2a^{2}} = \frac{\sinh (a(x))}{\sinh (a)} = \frac{x}{2a^{2}}; \quad (18)$$

(13) yields for the potential pro le

$$(0;z) = \frac{\sinh \frac{L}{2}}{2 \sinh (L=2)} :$$
 (19)

The deviation from the linear voltage drop can be quanti ed by inserting (17) into (16). Evaluating the sum, one nds

=
$$1 + 24\frac{2}{L^2}$$
 $9\frac{}{L}$ $\coth \frac{L}{2}$ $\frac{3}{2}\frac{1}{\sinh(L=2)}$: (20)

This result is shown in Fig. 2 as uppermost curve. In the lim it of very large screening length, ! 1, vanishes, thereby indicating the expected linear voltage drop. On the other hand, for very short screening length, ! 0, approaches one and the entire voltage drops at the interfaces between w ire and electrode.

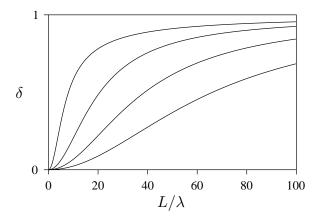


FIG. 2: The deviation (cf. (15)) of the voltage prole from the linear behavior is shown as a function of the ratio of wire length L and screening length . The four curves correspond to ! 1 (cf. (20)), =L = 0.05;0.02; and 0.01 from the upper to the lower curve.

For the case of nite width, we employ the Gaussian charge distribution

$$F(r_k) = \exp(r_k^2 = 2^2)$$
: (21)

This function is not normalized and therefore describes a charge distribution with a density in the center independent of the width . Such a situation arises when the diameter of a molecular layer can be controlled. Then, the charge density in the center appears in the screening length . In contrast, in the somewhat unrealistic case where the charge density on the wire is changed, the function $F\left(r_k\right)$ would have to be normalized.

One advantage of the Gaussian distribution (21) is the fact that the coe cients (14) may still be expressed analytically in terms of an exponential integral

$$F_n = \frac{1}{2} - e^{2} = \frac{Z_1}{u} = \frac{e^u}{u}$$
 (22)

with

$$= \frac{1}{2} 2 n_{T_1}^{2} : \qquad (23)$$

With this result the potential prole can be evaluated num erically according to (13) while the deviation from the linear voltage drop is obtained from (16).

In Fig. 2, the deviation of the voltage pro le from the linear behavior (8) is shown for di erent values of the wire thickness. The uppermost curve corresponds to the limit of a thick molecular layer! 1 which was discussed above. The three other curves correspond to =L = 0.05;0.02; and 0.01 from top to bottom. As these results demonstrate, a reduction of causes a reduction of indicating that the voltage pro le approaches the linear voltage drop. This behavior can be understood in terms of a reduction of screening due to the reduced

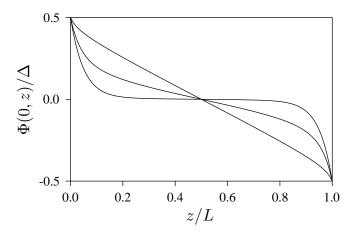


FIG. 3: The potential prole along a molecular wire computed from (13) and (22) is shown for a screening length =L = 0.05. The thickness parameter =L takes the values 0.0125;0.05; and 0.5 from the almost linear behavior to the voltage prole containing almost a plateau.

m olecular layer. However, this e ect becomes only relevant for L. As discussed above, the limit! 0 leads to a constant potential along the molecular wire. Therefore, all curves shown in Fig. 2 tend to = 1 in this limit even though this is not shown in the gure.

We now turn to a discussion of the voltage pro less them selves. Figure 3 depicts results obtained from (13) using F_n from (22) and $_0$ (z) as defined in (8). The dimensionless screening length =L=0.05 implies for a typical metallic screening length $=2\,a\,u$. a wire length of $L=20\,a\,u$. The thickness parameter =L for the three different curves are 0.0125;0.05; and 0.5, where the voltage pro le becomes more and more linear as decreases. As already mentioned, this may be understood in terms of the reduced screening. Fig. 4 shows similar results for a wire with a ratio between the typical diameter and the wire length of =L=0.125. Here, the dimensionless screening length takes the decreasing values =L=0.25;0.1; and 0.05 with increasing deviation from the linear voltage profile.

In Fig. 5 we present a tofour voltage pro leto the ab initio calculation of Ref. [6]. A least square t resulted in a screening length of =L=0.052 and a wire width of =L=0.032. For a distance L of approximately 34 a.u., this yields the reasonable value of 1.1 a.u. for the radial extent of the electron density.

The parameters =L and =L employed allow for a rather good approximation of the results of the ab initio calculation. However, there are two signicant differences. The Friedel oscillations found in the quantum calculation cannot be obtained within our classical approach. In a tight-binding model description of the molecular wire, Friedel oscillations naturally arise from a breaking of electron-hole symmetry [11]. Secondly, the systematic shift between the two voltage proles in Fig. 5 indicates that the wire in the ab initio calculation was

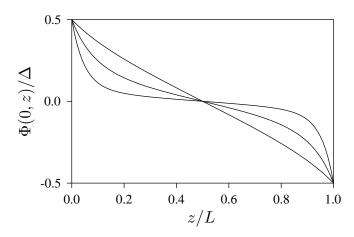


FIG. 4: Same as Fig. 3 but for xed thickness parameter =L = 0:125 and varying screening length =L = 0:25;0:1; and 0:05 from the alm ost linear behavior to the voltage pro le containing alm ost a plateau.

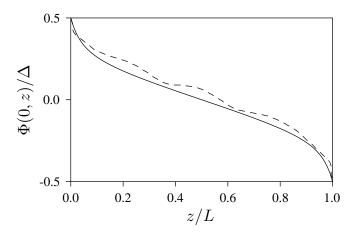


FIG. 5: The potential drop across a chain of 6 gold atoms placed between two gold electrodes as obtained from an ab inito calculation in Ref. [6] (dashed line) is tted by a voltage pro le (13) depicted as full line. The best twas obtained for =L=0.032 and =L=0.052.

charged while our wire is always assumed to be neutral. It is obvious from these results that the ratio of the wire thickness to the screening length does constitute an important generic attribute that determines the general behavior of the potential bias distribution along a molecular wire. The relatively good tobtained between the model calculations and the abinitio results for a chain of gold atoms using reasonable geometric parameters supports this conclusion. We note in passing that the at potential distribution observed [10] for metallic single

walled carbon nanotubes of thickness 20 a.u. is consistent with the results shown in Fig. 3. One should keep in m ind however that apart from its intrinsic simplicity, the model used in this work su ers from two important shortcom ings. Firstly, the use of a simple screening property as described by (1) and (2) cannot be justiled for all molecules, and certainly not for arbitrary distances. Even when such screening applies, the magnitude of the screening parameter is not known and is expected to depend on the amount of equilibrium charge transfer between the wire and the metalleads. Secondly, a complete calculation of the potential pro lealong am olecular junction should take into account the fact that some of this drop m ay take place on the m etal leads near the junction. Such a behavior was found in the calculation of Ref. [5].

V. CONCLUSIONS

The potential distribution along molecular wires in biased molecular junctions is determined in principle by the detailed electronic structure of the wire and by the response of this structure to the molecule-lead contacts and to the bias. The present study has identied the wire thickness as one of two generic attributes that largely determ ine the way the potential drops along the wire. Increasing this parameter leads to a crossover from a three-dimensional electrostatic problem to an eectively one-dimensional situation. The accompanying increase in screening causes a transition from a linear potential pro le to a situation where the potential drops mostly at the interfaces between wire and electrode. The other, less accessible molecular property is its ability to screen a local charge. In the present model calculation we have used a simple screening length parameter to model this m olecular property, but further studies are needed for a better characterization of this property.

A cknow ledgm ents

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